

Sample &

Buv



TPS22910A, TPS22912C, TPS22913B, TPS22913C

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TPS2291xx Ultra-small, Low On Resistance Load Switch With Controlled Turn-on

Technical

Documents

1 Features

- Integrated Single Load Switch
- Four Pin Wafer-Chip-Scale Package (Nom)
 - 0.9 mm × 0.9 mm, 0.5-mm Pitch, 0.5-mm Height (YZV)
- Input Voltage Range: 1.4 V to 5.5 V
- Low ON-Resistance
 - r_{ON} = 60 m Ω at VIN = 5 V
 - r_{ON} = 61 m Ω at VIN = 3.3 V
 - r_{ON} = 74 m Ω at VIN = 1.8 V
 - r_{ON} = 84 m Ω at VIN = 1.5 V
- 2-A Maximum Continuous Switch Current
- Low Threshold Control Input
- Controlled Slew-rate
- Under-Voltage Lock Out
- Full-Time Reverse Current Protection
- Quick Output Discharge Transistor (TPS22913B/C Devices)

2 Applications

- Notebook Computer and Ultrabook™
- Tablets and Set-Top-Boxes
- Portable Industrial / Medical Equipment
- Portable Media Players
- Point Of Sale Pins
- GPS Navigation Devices
- Digital Cameras
- Portable Instrumentation
- Smartphones / Wireless Handsets

3 Description

Tools &

Software

The TPS22910A, TPS22912C, and TPS22913B/C are small, low r_{ON} load switches with controlled turn on. The device contains a P-channel MOSFET that can operate over an input voltage range of 1.4 V to 5.5 V. The switch is controlled by an on/off input (ON), which is capable of interfacing directly with low-voltage GPIO control signals.

The TPS22910A, TPS22912C, and TPS22913B/C devices provide reverse current protection in ON and OFF states. An internal reverse voltage comparator disables the power-switch when the output voltage (V_{OUT}) is driven higher than the input voltage (V_{IN}), by V_{RCP} , to quickly (10 µs typ) stop the flow of current towards the input side of the switch. Reverse current protection is always active, even when the power-switch is disabled. Additionally, under-voltage lockout (UVLO) protection turns the switch off if the input voltage is too low.

The TPS22913B/C contains a 150- Ω on-chip load resistor for quick output discharge when the switch is turned off.

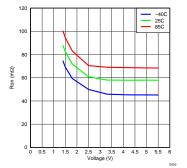
This family of devices have various slew rate options to avoid inrush current (see *Device Comparison Table* for details), are available in an ultra-small, space-saving 4-pin WCSP packages, and are characterized for operation over the free-air temperature range of -40° C to 85° C.

Device Information⁽¹⁾

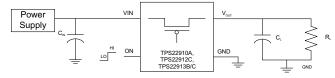
Dorido information						
PART NUMBER	PACKAGE	BODY SIZE (NOM)				
TPS22910A						
TPS22912C		0.00				
TPS22913B	DSBGA (4) 0.90 mm :	DODOA (4) 0.3	0.90 mm × 0.90 mm			
TPS22913C						

(1) For all available packages, see the orderable addendum at the end of the datasheet.

On-State Resistance vs Input Voltage



4 Simplified Schematic



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5 Revision History

Changes from Revision E (June 2014) to Revision F	Page
Updated 'ON' pin description in the Pin Functions table.	
Changes from Revision D (May 2014) to Revision E	Page
Updated Switching Characteristics table	
Updated Typical DC Characteristics section.	
Updated Timing Waveforms graphic.	
Updated Application Curves section.	
Changes from Revision C (May 2013) to Revision D	Page

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٠	Combined TPS22910A, TPS229	12C, and TPS22913B/C datasheets.	

2



6 Device Comparison Table

DEVICE	r _{ON} (typ) at 3.3 V	RISE TIME at 3.3V (typ)	QUICK OUTPUT DISCHARGE	MAXIMUM OUTPUT CURRENT	ENABLE
TPS22910A	61 mΩ	1 µs	No	2 A	Active Low
TPS22912C	61 mΩ	1000 µs	No	2 A	Active High
TPS22913B	61 mΩ	66 µs	Yes	2 A	Active High
TPS22913C	61 mΩ	660 µs	Yes	2 A	Active High

7 Pin Configuration and Functions

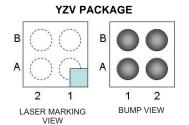


Table 1. Pin Assignments

В	ON	GND
Α	VIN	VOUT
	2	1

Pin Functions

	PIN	1/0	DESCRIPTION	
NAME	NO.	1/0	DESCRIPTION	
VOUT A1 O		0	Switch output	
VIN	VIN A2 I		Switch input, use a bypass capacitor (ceramic) to ground.	
GND	B1	_	– Ground	
ON	ON B2 I		Switch control input. Do not leave floating	

8 Specifications

8.1 Absolute Maximum Ratings

		MIN	MAX	UNIT
V _{IN}	Input voltage range	-0.3	6	V
V _{OUT}	Output voltage range	-0.3	6	V
V _{ON}	Input voltage range	-0.3	6	V
I _{MAX}	Maximum continuous switch current		2	А
I _{PLS}	Maximum pulsed switch current, pulse < 300 µs, 2% duty cycle		2.5	А
T _A	Operating free-air temperature range	-40	85	°C
TJ	Maximum junction temperature		125	°C
T _{stg}	Storage temperature range	-65	150	°C

8.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 $^{\rm (2)}$	±1000	V

 JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 500-V HBM is possible with the necessary precautions. Pins listed as ±2000 V may actually have higher performance.
JEDEC document JEP157 states that 500 V COM allows and actually have higher performance.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 250-V CDM is possible with the necessary precautions. Pins listed as ±1000 V may actually have higher performance.

8.3 Recommended Operating Conditions

			MIN	MAX	UNIT
V _{IN}	Input voltage range		1.4	5.5	V
V _{ON}	ON voltage range		0	5.5	V
V _{OUT}	Output voltage range			V _{IN}	
VIH	High-level input voltage, ON	VIN = 1.4 V to 5.5 V	1.1	5.5	V
V		VIN = 3.61 V to 5.5 V		0.6	V
V _{IL}	Low-level input voltage, ON	VIN = 1.4 V to 3.6 V		0.4	V
CIN	Input capacitor	·	1 ⁽¹⁾		μF

(1) Refer to the application section.

8.4 Thermal Information

		TPS22910	TPS22912	TPS22913	
	THERMAL METRIC ⁽¹⁾	CSP	CSP	CSP	UNIT
		4 PINS	4 PINS	4 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	189.1	189.1	189.1	
R _{0JCtop}	Junction-to-case (top) thermal resistance	1.9	1.9	1.9	
$R_{\theta JB}$	Junction-to-board thermal resistance	36.8	36.8	36.8	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	11.3	11.3	11.3	
Ψ _{JB}	Junction-to-board characterization parameter	36.8	36.8	36.8	

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

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8.5 Electrical Characteristics

The electrical characteristics in this section apply to all devices unless otherwise noted. For TPS22910A $V_{ON} = 0$ V where enabled and $V_{ON} = V_{IN}$ where disabled. For TPS22912C and TPS22913B/C $V_{ON} = V_{IN}$ where enabled and $V_{ON} = 0$ V where disabled. $V_{IN} = 1.4$ V to 5.5 V, $T_A = -40^{\circ}$ C to 85°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
		$I_{OUT} = 0$ mA, $V_{IN} = 5.25$ V, $V_{ON} =$ Enabled			2	10	
		$I_{OUT} = 0$ mA, $V_{IN} = 4.2$ V, $V_{ON} =$ Enabled			2	7.0	
I _{IN}	Quiescent current	$I_{OUT} = 0$ mA, $V_{IN} = 3.6$ V, $V_{ON} =$ Enabled	Full		2	7.0	μA
		$I_{OUT} = 0$ mA, $V_{IN} = 2.5$ V, $V_{ON} =$ Enabled			0.9	5	
		$I_{OUT} = 0$ mA, $V_{IN} = 1.5$ V, $V_{ON} =$ Enabled			0.7	5	
		R_L = 1 MΩ, V_{IN} = 5.25 V, V_{ON} = Disabled			1.2	10	
		R_L = 1 MΩ, V_{IN} = 4.2 V, V_{ON} = Disabled			0.2	7.0	
I _{IN(off)}	Off supply current	R_L = 1 MΩ, V_{IN} = 3.6 V, V_{ON} = Disabled	Full		0.1	7.0	μA
		R_L = 1 MΩ, V_{IN} = 2.5 V, V_{ON} = Disabled			0.1	5	
		R_L = 1 MΩ, V_{IN} = 1.5 V, V_{ON} = Disabled			0.1	5	
		V_{OUT} = 0 V, V_{IN} = 5.25 V, V_{ON} = Disabled			1.2	10	
		V_{OUT} = 0 V, V_{IN} = 4.2 V, V_{ON} = Disabled			0.2	7.0	
I _{IN(Leakage)}	Leakage current	V_{OUT} = 0 V, V_{IN} = 3.6 V, V_{ON} = Disabled	Full		0.1	7.0	μA
		V_{OUT} = 0 V, V_{IN} = 2.5 V, V_{ON} = Disabled			0.1	5	
		V_{OUT} = 0 V, V_{IN} = 1.5 V, V_{ON} = Disabled			0.1	5	
		\/	25°C		60	80	mΩ
		$V_{IN} = 5.25 \text{ V}, I_{OUT} = -200 \text{ mA}$	Full			110	
		V _{IN} = 5.0 V, I _{OUT} = -200 mA	25°C		60	80	
			Full			110	
		V _{IN} = 4.2 V, I _{OUT} = -200 mA	25°C		60	80	
			Full			110	
*	On registance	V 22V L 200 mA	25°C		60.7	80	
r _{ON}	On-resistance	$V_{IN} = 3.3 \text{ V}, I_{OUT} = -200 \text{ mA}$	Full			110	
		V _{IN} = 2.5 V, I _{OUT} = -200 mA	25°C		63.4	90	
			Full			120	
			25°C		74.2	100	
		V _{IN} = 1.8 V, I _{OUT} = -200 mA	Full			130	
		V _{IN} = 1.5 V, I _{OUT} = -200 mA	25°C		83.9	120	
		$v_{\rm IN} = 1.5 v, v_{\rm OUT} = -200 {\rm mA}$	Full			150	
RPD ⁽¹⁾	Output pull down resistance	$V_{IN} = 3.3 \text{ V}, I_{OUT} = 30 \text{ mA}, V_{ON} = 0$	25°C		153	200	Ω
		V_{IN} increasing, $V_{ON} = 0 V$,				1.2	
UVLO	Under voltage lockout	I _{OUT} = -100 mA	Full			1.2	V
		V_{IN} decreasing, V_{ON} = 0 V, R_L = 10 Ω		0.50			
I _{ON}	ON input leakage current	V _{ON} = 1.4 V to 5.25 V or GND	Full			1	μA
V _{RCP}	Reverse current voltage	TPS22910A, TPS22913B/C			44		mV
	threshold	TPS22912C			54		
t _{DELAY}	Reverse current response delay	V _{IN} = 5 V			10		μs
I _{RCP} (leak)	Reverse current protection leakage after reverse current event.	$V_{OUT} - V_{IN} > V_{RCP}$	25°C		0.3		μA

(1) Only applies to the TPS22913B/C devices

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8.6 Switching Characteristics, Typical

	PARAMETER	TEST CONDITION	TPS22910A	TPS22912C	TPS22913B	TPS22913C	UNIT
VIN = 5	V, T _A = 25⁰C (unless othe	rwise noted)					
t _{ON}	Turn-ON time	$R_L = 10 \ \Omega, \ C_L = 0.1 \ \mu F$	2	840	76	770	
t _{OFF}	Turn-OFF time	$R_L = 10 \ \Omega, \ C_L = 0.1 \ \mu F$	5.5	6.6	6.6	6.6	1
t _R	VOUT rise time	$R_L = 10 \ \Omega, \ C_L = 0.1 \ \mu F$	1	912	82	838	μs
t _F	VOUT fall time	$R_L = 10 \ \Omega, \ C_L = 0.1 \ \mu F$	3	3	3	3	
VIN = 3	8.3 V, T _A = 25⁰C (unless oth	nerwise noted)					
t _{ON}	Turn-ON time	$R_L = 10 \ \Omega, \ C_L = 0.1 \ \mu F$	2.5	1147	102	1048	
t _{OFF}	Turn-OFF time	$R_L = 10 \ \Omega, \ C_L = 0.1 \ \mu F$	7	8.6	8.5	8.6	1
t _R	VOUT rise time	$R_L = 10 \ \Omega, \ C_L = 0.1 \ \mu F$	1	1030	97	980	μs
t _F	VOUT fall time	$R_L = 10 \Omega, C_L = 0.1 \mu F$	3.5	3	3	3	
VIN = 1	.5 V, T _A = 25°C (unless oth	nerwise noted)		1			а
t _{ON}	Turn-ON time	$R_L = 10 \Omega, C_L = 0.1 \mu F$	4.5	2513	234	2344	
t _{OFF}	Turn-OFF time	$R_L = 10 \Omega, C_L = 0.1 \mu F$	16.5	17.4	17	18	
t _R	VOUT rise time	$R_L = 10 \ \Omega, \ C_L = 0.1 \ \mu F$	2	1970	244	1823	μs
t _F	VOUT fall time	R _L = 10 Ω, C _L = 0.1 μF	7	6.5	6.5	6.5	1

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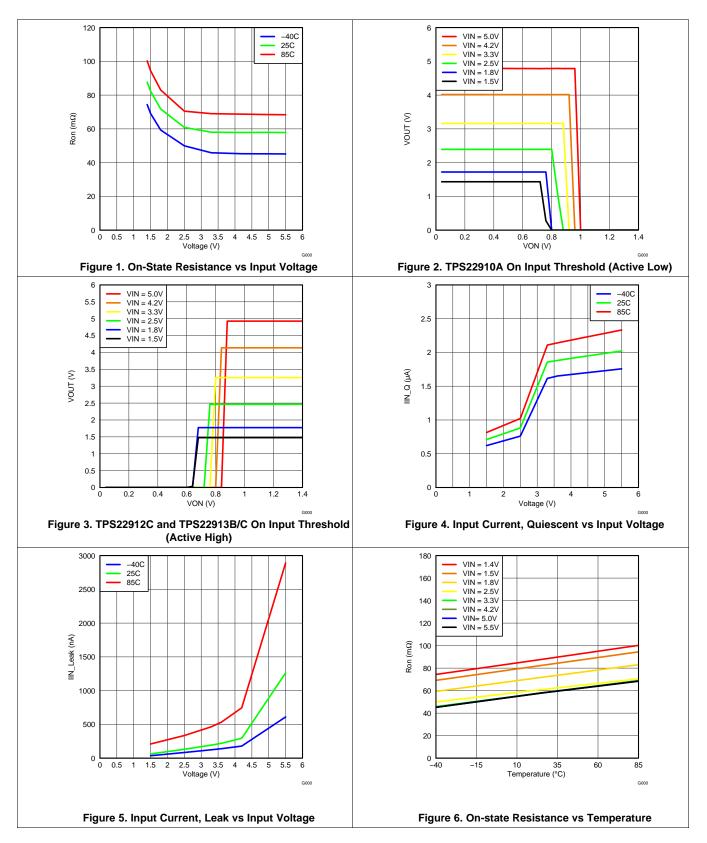


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8.7 Typical DC Characteristics

The typical characteristics curves in this section apply to all devices unless otherwise noted.



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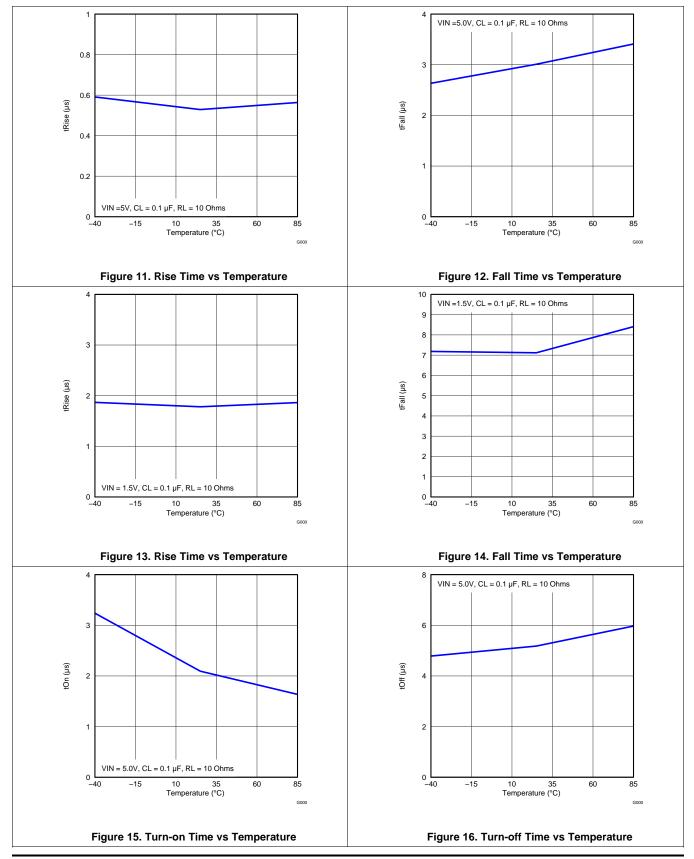
Typical DC Characteristics (continued)

1 800 -40C 25C 85C 0.9 Maximum Power Dissipation (W) 700 0.8 0.7 600 0.6 500 0.5 IIN_Off (nA) 0.4 400 0.3 300 0.2 0.1 200 0 -40 -30 -20 -10 0 10 20 30 40 50 60 70 80 100 Ambient Temperature (°C) G001 0 0.5 1 1.5 2 2.5 3 3.5 Voltage (V) 4 4.5 5 5.5 6 G067 Figure 8. Allowable Power Dissipation Figure 7. Input Current, Off vs Input Voltage Te<u>k Run</u> Trig'd Te<u>k</u> PreVu Trig? -20.74ms 74.26ms ∆95.00ms 800.0mV 800.0mV ∆0.000 V –1.124ms –27.32µs ∆1.096ms 41.50mV 68.84mV 8 0 0 ∆27.34mV IT. 1 VIN 🚯 νουτ – 🗤 1.00ms 100MS/s 1 500mA Ω 3 100mV 1 ጊ 200mA 50.0kS/s 10k points 7 Jun 2014 05:29:59 (**1**) 1.00 V 20.0ms 1M points **1** *J* 2.92 V Min 149.1m Value 1.133 A Mean 887.1m Max 1.133 Std Dev 🛑 Max Figure 9. Under Voltage Lockout Response Figure 10. Full-Time Reverse Current Protection (IOUT = -100mA)(VIN = 3.0 V, VOUT Ramp up From 3.0 V to 3.3 V)

The typical characteristics curves in this section apply to all devices unless otherwise noted.



8.8 Typical AC Characteristics, TPS22910A



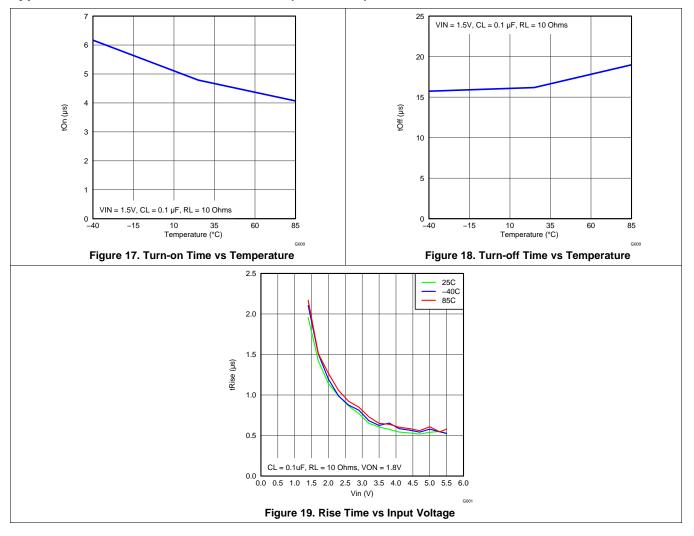
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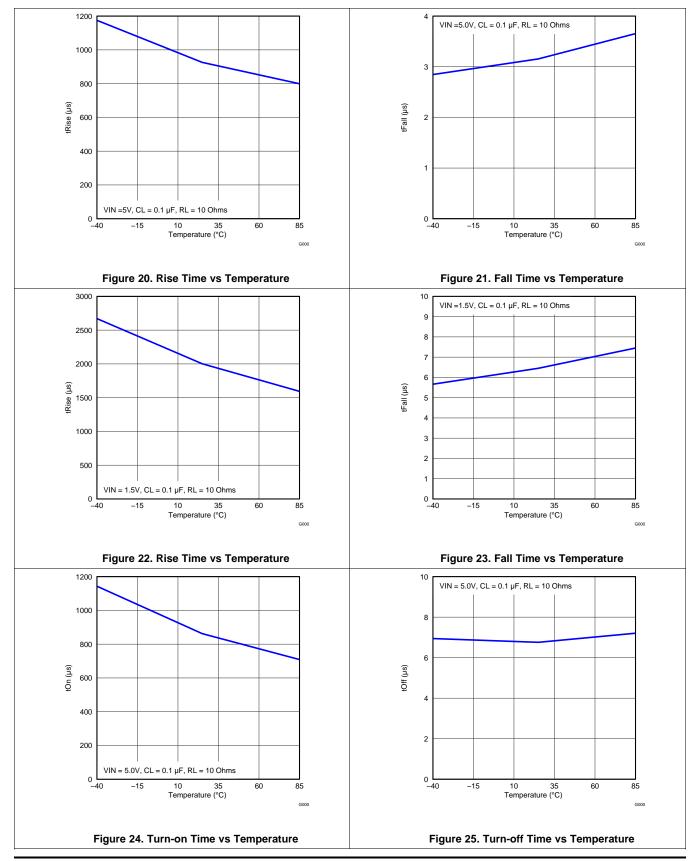


Typical AC Characteristics, TPS22910A (continued)





8.9 Typical AC Characteristics, TPS22912C

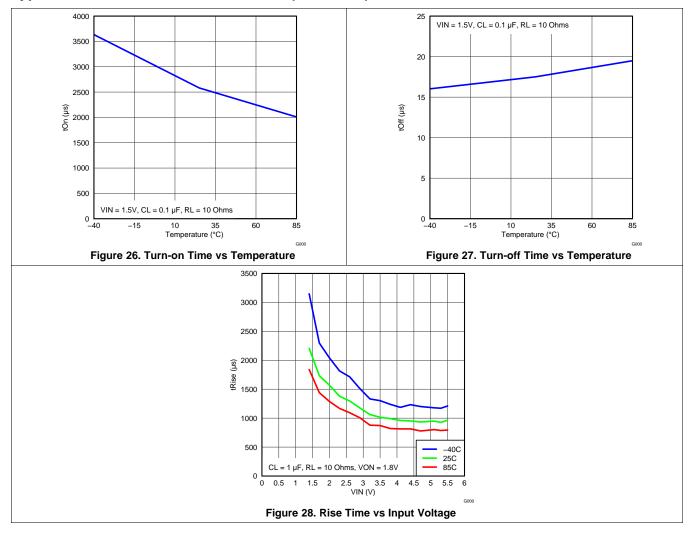


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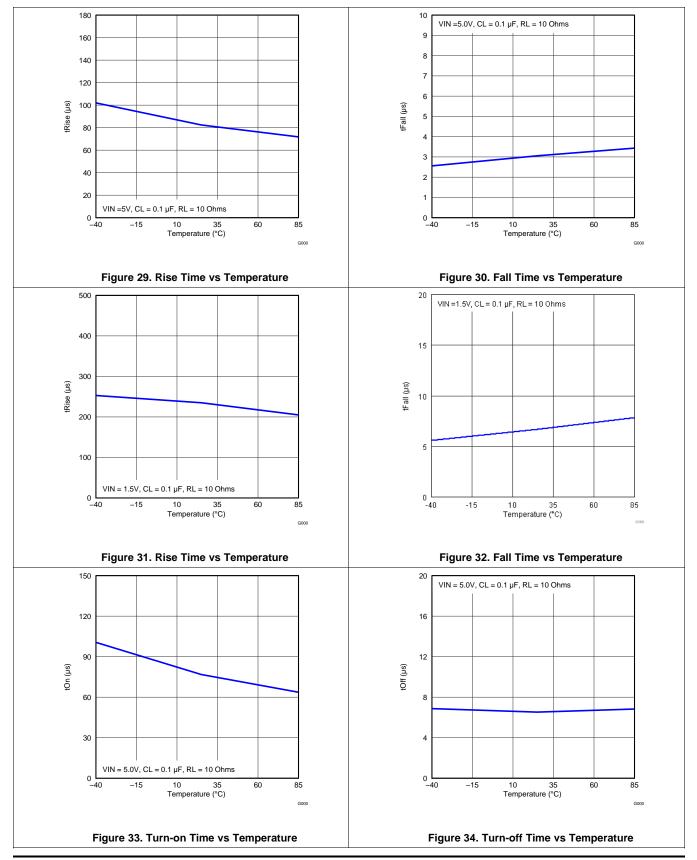


Typical AC Characteristics, TPS22912C (continued)





8.10 Typical AC Characteristics, TPS22913B

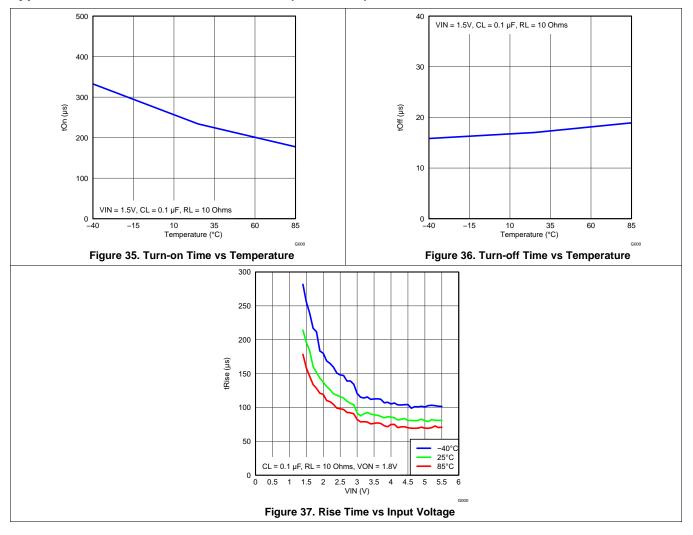


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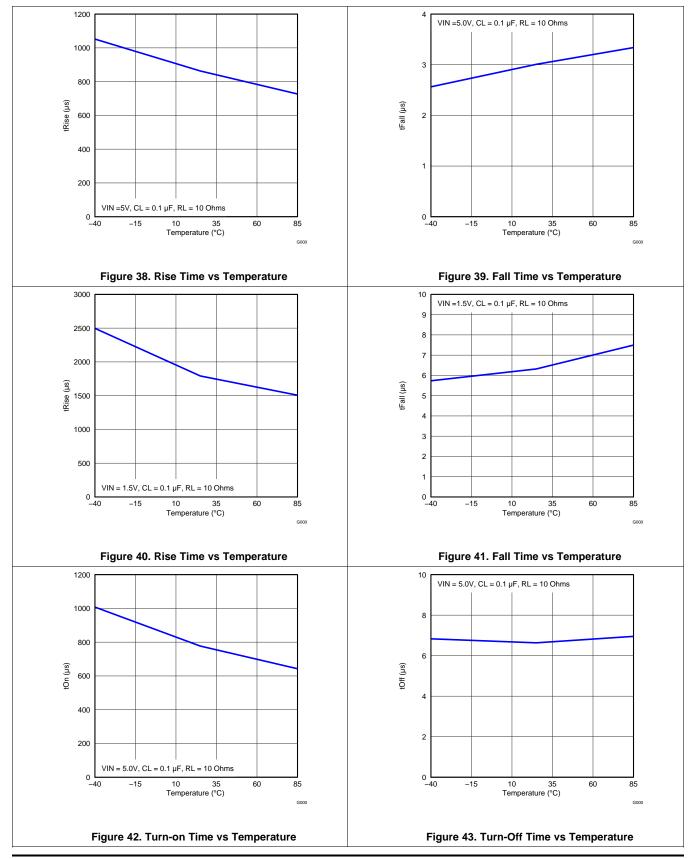


Typical AC Characteristics, TPS22913B (continued)





8.11 Typical AC Characteristics, TPS22913C

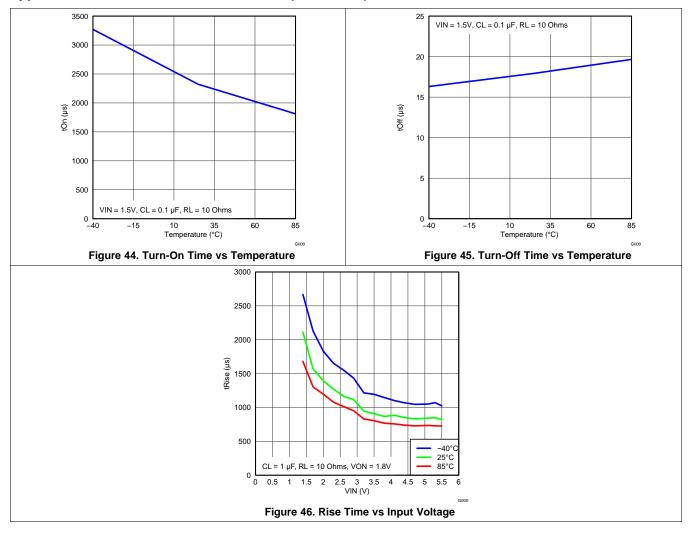


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Typical AC Characteristics, TPS22913C (continued)





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9 Parameter Measurement Information

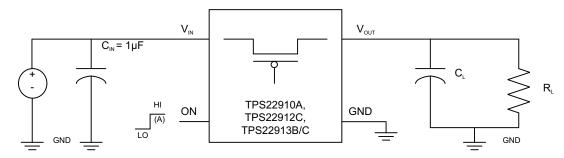
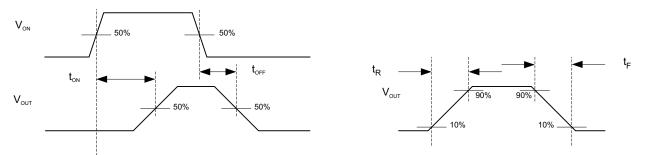


Figure 47. Timing Test Circuit



A. Rise and fall times of the control signal is 100 ns.

Figure 48. Timing Waveforms

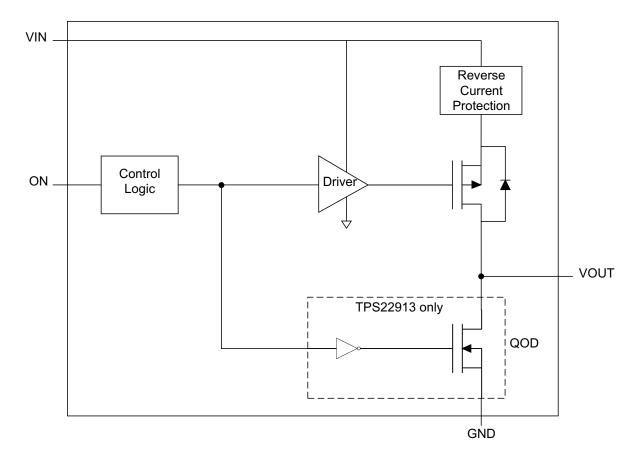
10 Detailed Description

10.1 Overview

This family of devices are single channel, 2-A load switches in ultra-small, space saving 4-pin WCSP package. These devices implement a low resistance P-channel MOSFET with a controlled rise time for applications that need to limit the inrush current.

These devices are designed to have very low leakage current during off state. This prevents downstream circuits from pulling high standby current from the supply. Integrated control logic, driver, power supply, and output discharge FET eliminates the need for additional external components, which reduces solution size and BOM count.

10.2 Functional Block Diagram



10.3 Feature Description

10.3.1 On/Off Control

The ON pin controls the state of the switch. The ON pin is compatible with standard GPIO logic threshold. It can be used with any microcontroller with 1.2-V, 1.8-V, 2.5-V, 3.3-V, or 5.5-V GPIO.

10.3.2 Under-Voltage Lockout

Under-voltage lockout protection turns off the switch if the input voltage drops below the under-voltage lockout threshold (UVLO). With the ON pin active, the input voltage rising above the under-voltage lockout threshold will cause a controlled turn-on of the switch to limit current over-shoot.



Feature Description (continued)

10.3.3 Full-Time Reverse Current Protection

In a scenario where V_{OUT} is greater than V_{IN} , there is potential for reverse current to flow through the pass FET or the body diode. The devices monitor V_{IN} and V_{OUT} voltage levels. When the reverse current voltage threshold (V_{RCP}) is exceeded, the switch is disabled (within 10µs typ). Additionally, the body diode is disengaged so as to prevent any reverse current flow to VIN. The peak instantaneous reverse current is the current it takes to activate the reverse current protection. After the reverse current protection has activated due to the peak instantaneous reverse current, the DC (off-state) leakage current from V_{OUT} and V_{IN} is referred to as I_{RCP} (leak) (see Figure 49). The pass FET, and the output voltage (V_{OUT}), will resume normal operation when the reverse voltage scenario is no longer present.

The following formula can be used to calculate the amount of peak instantaneous reverse current for a particular application:

$$I_{\rm RC} = \frac{V_{\rm RCP}}{r_{\rm ON(VIN)}}$$

Where,

 \mathbf{I}_{RC} is the amount of reverse current,

 $r_{ON(VIN)}$ is the on-resistance at the VIN of the reverse current condition.

V_{RCP} is the reverse voltage threshold.

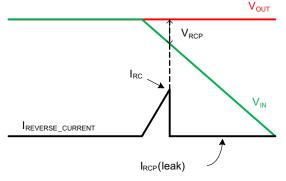


Figure 49. Reverse Current

10.4 Device Functional Modes

Table 2 describes what the VOUT pin will be connected to for a particular device as determined by the ON pin

Table 2. VOUT Function Table	Table	2.	VOUT	Function	Table
------------------------------	-------	----	------	----------	-------

ON	TPS22910A	TPS22912C	TPS22913B/C
L	VIN	Open	GND
Н	Open	VIN	VIN

Application and Implementation

11.1 Application Information

This section will highlight some of the design considerations when implementing this device in various applications. A PSPICE model for this device is also available in the product page of this device on www.ti.com for further aid.

11.1.1 VIN to VOUT Voltage Drop

The VIN to VOUT voltage drop in the device is determined by the R_{ON} of the device and the load current. The R_{ON} of the device depends upon the VIN condition of the device. Refer to the R_{ON} specification of the device in the Electrical Characteristics table of this datasheet. Once the R_{ON} of the device is determined based upon the VIN conditions, use Equation 1 to calculate the VIN to VOUT voltage drop:

 $\Delta V = I_{LOAD} \times R_{ON}$

(1)

Where,

11

 ΔV = Voltage drop from VIN to VOUT

 $I_{I,OAD}$ = Load current

 R_{ON} = On-resistance of the device for a specific V_{IN}

An appropriate I_{LOAD} must be chosen such that the I_{MAX} specification of the device is not violated.

11.1.2 On/Off Control

The ON pin controls the state of the switch. The ON pin has a low threshold, making it capable of interfacing with low-voltage signals. The ON pin is compatible with standard GPIO logic thresholds. It can be used with any microcontroller with 1.2 V or higher GPIO voltage. This pin cannot be left floating and must be driven either high or low for proper functionality.

11.1.3 Input Capacitor (Optional)

To limit the voltage drop on the input supply caused by transient inrush currents when the switch turns on into a discharged load capacitor or short-circuit, a capacitor needs to be placed between V_{IN} and GND. A 1- μ F ceramic capacitor, C_{IN} , placed close to the pins, is usually sufficient. Higher values of C_{IN} can be used to further reduce the voltage drop during high current applications. When switching heavy loads, it is recommended to have an input capacitor about 10 times higher than the output capacitor to avoid excessive voltage drop.

11.1.4 Output Capacitor (Optional)

Due to the integrated body diode in the PMOS switch, a C_{IN} greater than C_L is highly recommended. A C_L greater than C_{IN} can cause V_{OUT} to exceed V_{IN} when the system supply is removed. This could result in current flow through the body diode from V_{OUT} to V_{IN} . A C_{IN} to C_L ratio of 10 to 1 is recommended for minimizing VIN dip caused by inrush currents during startup, however a 10 to 1 ratio for capacitance is not required for proper functionality of the device. A ratio smaller than 10 to 1 (such as 1 to 1) could cause slightly more V_{IN} dip upon turn-on due to inrush currents. This can be mitigated by using a device with a longer rise time.

11.2 Typical Application

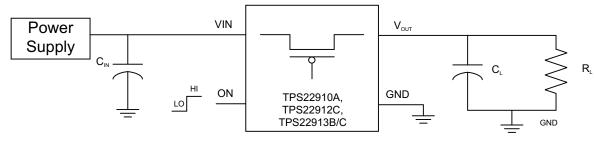


Figure 50. Typical Application



Typical Application (continued)

11.2.1 Design Requirements

Design Parameter	Example Value
VIN	1.5 V to 5 V
CL	0.1 μF to 1 μF
Maximum Acceptable Inrush Current	1 A

11.2.2 Detailed Design Procedure

11.2.2.1 Inrush Current

When the switch is enabled, the output capacitors must be charged up from 0-V to VIN voltage. This charge arrives in the form of inrush current. Inrush current can be calculated using the following equation:

Inrush Current =
$$C \times \frac{dv}{dt}$$
 (2)

Where,

C = Output capacitance

$$\frac{dv}{dt}$$
 = Output slew rate

The TPS22910A, TPS22912C, and TPS22913B/C offer several different rise time options to control the inrush current during turn-on. The appropriate device can be selected based upon the maximum acceptable slew rate which can be calculated using the design requirements and the inrush current equation. An output capacitance of $1.0 \ \mu\text{F}$ will be used since the inrush follows the following equations:

1.0 A = 1.0
$$\mu$$
F × $\frac{dv}{dt}$ (3)
 $\frac{dv}{dt} = 1 \text{ V/}\mu\text{s}$ (4)

To ensure an inrush current of less than 1 A, a device with a slew rate less than 1 V/µs must be used

The TPS22910A has a typical rise time of 1 μ s at 3.3 V. This results in a slew rate of 3.3 V/ μ s which is above the 1 V/ μ s requirement meaning the TPS22910 could not be used to meet the design requirements.

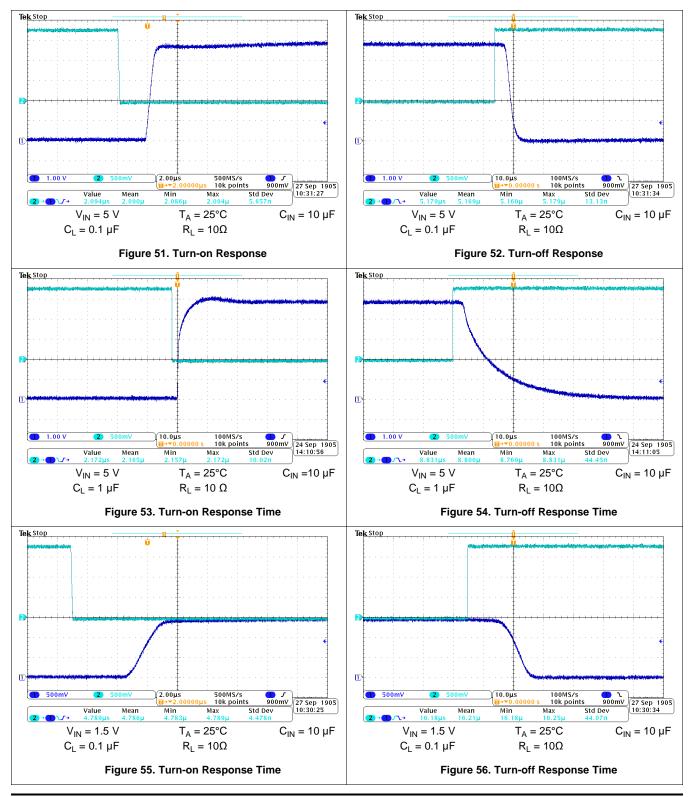
The TPS22913B has a typical rise time of 66 μ s at 3.3 V. This results in a slew rate of 50 mV/ μ s which is below the 1 V/ μ s requirement; therefor, the TPS22913B could be used to meet the design requirements. The TPS22912C or TPS22913C have lower slew rates than the TPS22913B, so they could also be used, but the output would rise more slowly.



11.2.3 Application Curves

11.2.3.1 Typical Application Characteristics for TPS22910A

The dark blue curve (Channel 1) represents the VOUT pin of the device. The light blue curve (Channel 2) represents the ON pin of the device.



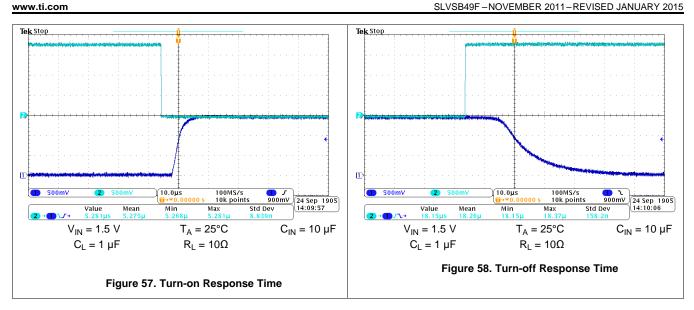
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TPS22910A, TPS22912C, TPS22913B, TPS22913C

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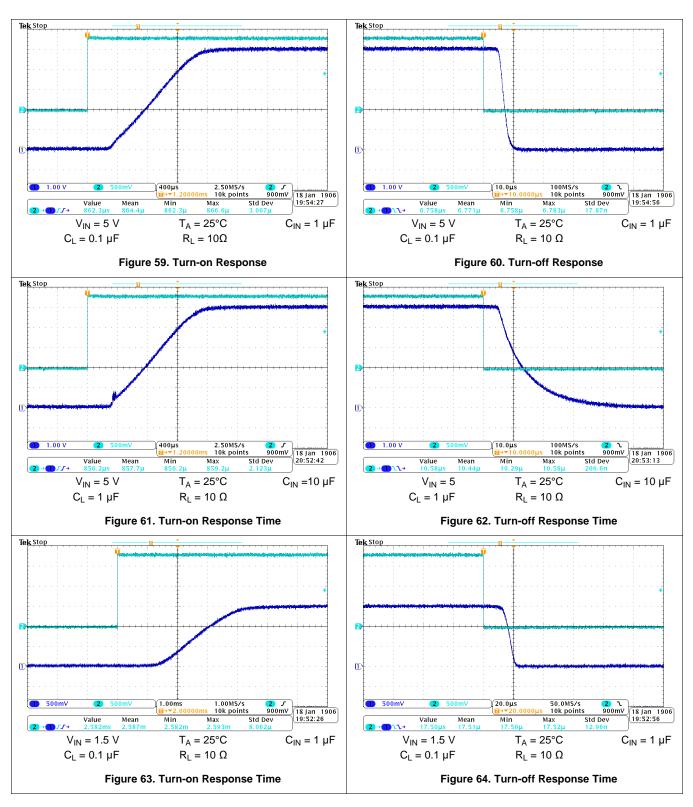
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11.2.3.2 Typical Application Characteristics for TPS22912C

The dark blue curve (Channel 1) represents the VOUT pin of the device. The light blue curve (Channel 2) represents the ON pin of the device.



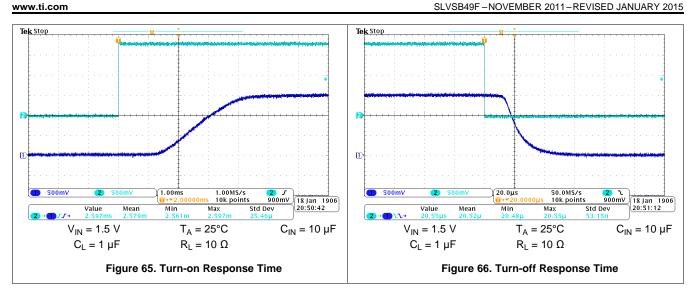
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TPS22910A, TPS22912C, TPS22913B, TPS22913C

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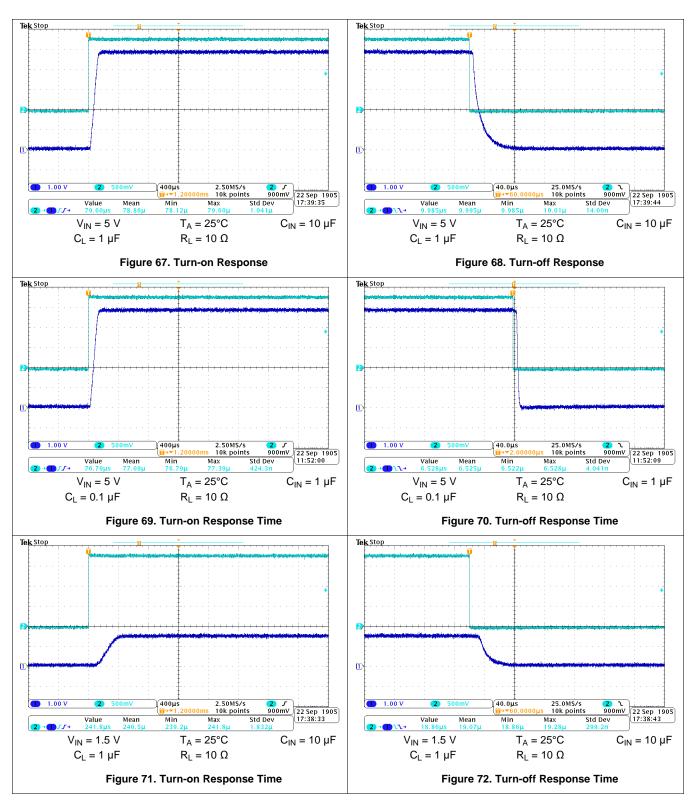




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11.2.3.3 Typical Application Characteristics For TPS22913B

The dark blue curve (Channel 1) represents the VOUT pin of the device. The light blue curve (Channel 2) represents the ON pin of the device.



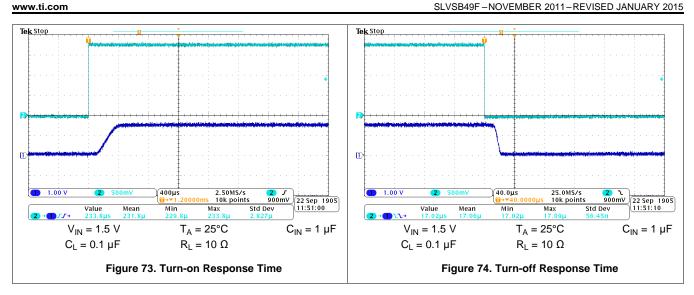
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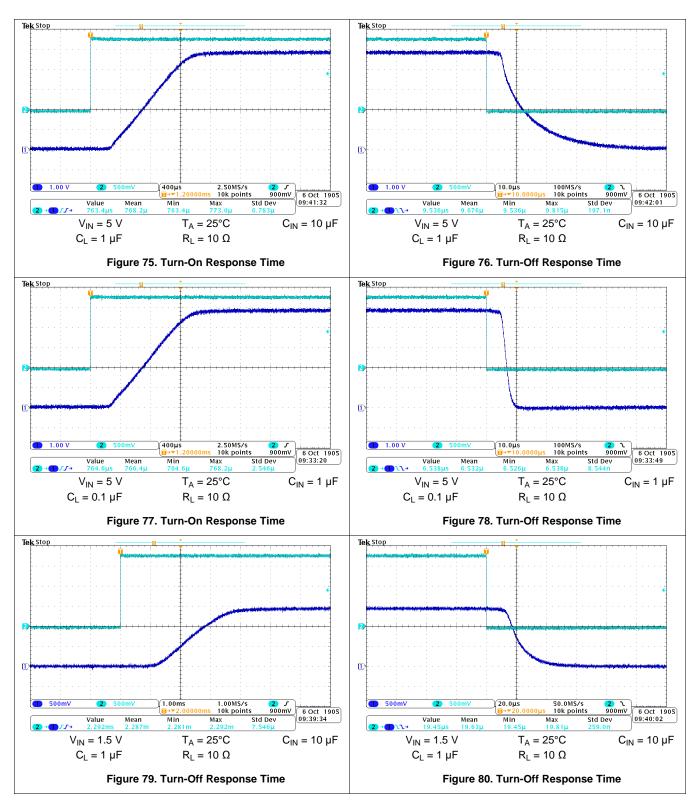




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11.2.3.4 Typical Application Characteristics for TPS22913C

The dark blue curve (Channel 1) represents the VOUT pin of the device. The light blue curve (Channel 2) represents the ON pin of the device.



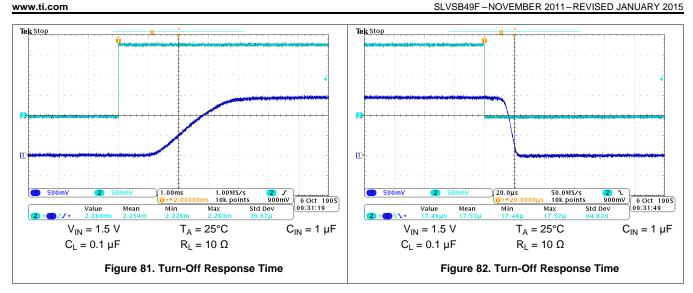
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TPS22910A, TPS22912C, TPS22913B, TPS22913C

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12 Power Supply Recommendations

The device is designed to operate with a VIN range of 1.4 V to 5.5 V.

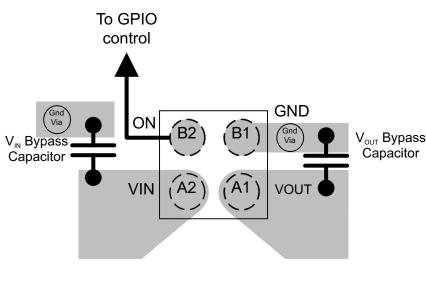
13 Layout

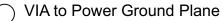
13.1 Layout Guidelines

For best performance, all traces should be as short as possible. To be most effective, the input and output capacitors should be placed close to the device to minimize the effects that parasitic trace inductances may have on normal operation. Using wide traces for VIN, VOUT, and GND helps minimize the parasitic electrical effects along with minimizing the case to ambient thermal impedance.

13.2 Layout Example

The figure below shows an example for these devices. Notice the connection to system ground between the V_{OUT} Bypass Capacitor ground and the GND pin of the load switch, this creates a ground barrier which helps to reduce the ground noise seen by the device.





13.3 Thermal Considerations

The maximum IC junction temperature should be restricted to 125°C under normal operating conditions. To calculate the maximum allowable dissipation, $P_{D(max)}$ for a given output current and ambient temperature, use the following equation as a guideline:

$$\mathsf{P}_{\mathsf{D}(\mathsf{MAX})} = \frac{\mathsf{T}_{\mathsf{J}(\mathsf{MAX})} - \mathsf{T}_{\mathsf{A}}}{\mathsf{R}_{\mathsf{\theta}\mathsf{J}\mathsf{A}}}$$

where

- P_{D(max)} = maximum allowable power dissipation
- T_{J(max)} = maximum allowable junction temperature
- T_A = ambient temperature of the device
- θ_{JA} = junction to air thermal impedance. See the *Thermal Information* section. This parameter is highly dependent upon board layout.

(5)

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14 Device and Documentation Support

14.1 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
TPS22910A	Click here	Click here	Click here	Click here	Click here
TPS22912C	Click here	Click here	Click here	Click here	Click here
TPS22913B	Click here	Click here	Click here	Click here	Click here
TPS22913C	Click here	Click here	Click here	Click here	Click here

Table 3. Related Links

14.2 Trademarks

Ultrabook is a trademark of Intel. All other trademarks are the property of their respective owners.

14.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

14.4 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

15 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



1-Dec-2015

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TPS22910AYZVR	ACTIVE	DSBGA	YZV	4	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	75	Samples
TPS22910AYZVT	ACTIVE	DSBGA	YZV	4	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	75	Samples
TPS22912CYZVR	ACTIVE	DSBGA	YZV	4	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	78	Samples
TPS22912CYZVT	ACTIVE	DSBGA	YZV	4	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	78	Samples
TPS22913BYZVR	ACTIVE	DSBGA	YZV	4	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	64	Samples
TPS22913BYZVT	ACTIVE	DSBGA	YZV	4	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	64	Samples
TPS22913CYZVR	ACTIVE	DSBGA	YZV	4	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	76	Samples
TPS22913CYZVT	ACTIVE	DSBGA	YZV	4	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	76	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.



1-Dec-2015

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS22910AYZVR	DSBGA	YZV	4	3000	178.0	9.2	1.0	1.0	0.63	4.0	8.0	Q1
TPS22910AYZVT	DSBGA	YZV	4	250	178.0	9.2	1.0	1.0	0.63	4.0	8.0	Q1
TPS22912CYZVR	DSBGA	YZV	4	3000	178.0	9.2	1.0	1.0	0.63	4.0	8.0	Q1
TPS22912CYZVT	DSBGA	YZV	4	250	178.0	9.2	1.0	1.0	0.63	4.0	8.0	Q1
TPS22913BYZVR	DSBGA	YZV	4	3000	180.0	8.4	1.0	1.0	0.63	4.0	8.0	Q1
TPS22913BYZVR	DSBGA	YZV	4	3000	178.0	9.2	1.0	1.0	0.63	4.0	8.0	Q1
TPS22913BYZVT	DSBGA	YZV	4	250	178.0	9.2	1.0	1.0	0.63	4.0	8.0	Q1
TPS22913CYZVR	DSBGA	YZV	4	3000	178.0	9.2	1.0	1.0	0.63	4.0	8.0	Q1
TPS22913CYZVT	DSBGA	YZV	4	250	178.0	9.2	1.0	1.0	0.63	4.0	8.0	Q1

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PACKAGE MATERIALS INFORMATION

12-Aug-2016



*All dimensions are nominal							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS22910AYZVR	DSBGA	YZV	4	3000	220.0	220.0	35.0
TPS22910AYZVT	DSBGA	YZV	4	250	220.0	220.0	35.0
TPS22912CYZVR	DSBGA	YZV	4	3000	220.0	220.0	35.0
TPS22912CYZVT	DSBGA	YZV	4	250	220.0	220.0	35.0
TPS22913BYZVR	DSBGA	YZV	4	3000	182.0	182.0	20.0
TPS22913BYZVR	DSBGA	YZV	4	3000	220.0	220.0	35.0
TPS22913BYZVT	DSBGA	YZV	4	250	220.0	220.0	35.0
TPS22913CYZVR	DSBGA	YZV	4	3000	220.0	220.0	35.0
TPS22913CYZVT	DSBGA	YZV	4	250	220.0	220.0	35.0



- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.

NanoFree is a trademark of Texas Instruments.



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